

View Online at <https://aerobasegroup.com/nsn/5980-01-351-4897>

General Description:

Gallium-arsenide light emitting diode optically coupled to a planar silicon npn darlington phototransistor both of which are in a plastic case; reverse voltage 3.0 volts for l e d; collector-emitter breakdown voltage 30.0 for phototransistor; power dissipation 90.0mw; 0.450 in.

Maximum lg; 0.280 in. Maximum w; 0.200 in. Maximum h

Shelf Life:

N/a

Unit Of Measure:

--

Demilitarization:

Yes - demil/mli

Fig:

A23900